L Number	Hits	Search Text	DB	Time stamp
1	21	(("4292093") or ("4942058") or ("5024968") or ("5352291") or	USPAT;	2003/01/07 15:36
		; ("5372836") or ("5424244") or ("5529630") or ("5593497") or ; ("5843225") or ("5842833")).PN.	US-PGPUB; EPO; JPO;	
		( 3043223 ) 01 ( 3042033 )).FN.	DERWENT:	
			IBM_TDB	
2	2	("5405804").PN.	USPAT:	2003/01/07 15:36
			US-PGPUB;	1
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795)	USPAT;	2003/01/07 11:18
		or (438/909) or (438/for.200) or (438/for.269) or (438/for.334)	US-PGPUB;	
		or (117/8) or (117/9) or (117/10)).CCLS.	EPO; JPO; DERWENT:	
			IBM_TDB	
	2937	laser with crystallization	USPAT:	2003/01/06 10:07
1	2001	idoor With ory old in Edition	US-PGPUB:	2000/01/00 10:07
ì			EPO; JPO;	
1			DERWENT;	i
			IBM_TDB	
·	1421	(laser with crystallization) and laser with anneal\$3	USPAT;	2003/01/07 11:17
i			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	1379	((laser with epictallization) and lacer with appeal\$3) and	IBM_TDB	2003/01/03 10:59
-	13/9	((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)	USPAT; US-PGPUB;	2003/01/03 10.58
		(sincon seniconductor)	EPO; JPO;	-
			DERWENT;	
1			IBM_TDB	
-	96	(((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 11:00
		(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))	US-PGPUB;	İ
			EPO; JPO;	
			DERWENT;	
	50	((((1,	IBM_TDB	0000/04/00 44:04
-	52	((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 14:34
		(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4	US-PGPUB; EPO; JPO;	
4		Glean y	DERWENT:	1
			IBM_TDB	
- !	5	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 11:35
į		(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and	US-PGPUB;	i
í		clean\$4) and @ad<=19951025	EPO; JPO;	1
	i		DERWENT;	į
	2	(((C240200)) DAI	IBM_TDB	: 2002/04/02 44:20
-	2	("6348369").PN.	USPAT; US-PGPUB;	2003/01/03 11:36
]			EPO; JPO;	
1			DERWENT:	
	}		IBM_TDB	
	3	("4180618"   "4851363"   "5064779").PN.	USPAT	2003/01/03 13:30
. 1	25	4180618.URPN.	USPAT	2003/01/03 13:32
	6	5344796.URPN.	USPAT	2003/01/03 13:56
	9	("3998980"   "4222814"   "5242707"   "5337207"   "5344796"	USPAT	2003/01/03 13:59
1		"5434102"   "5587343"   "5757061"   "5834803").PN.		
•	3	("4180618"   "4851363"   "5064779").PN.	USPAT	2003/01/03 14:09
•	25	4180618.URPN.	USPAT	2003/01/03 14:09
	6	("4019169"   "4180618"   "4643950"   "4732801"   "4795679"	USPAT	2003/01/03 14:10
	16	"4847157").PN. 5108843.URPN.	USPAT	2003/01/03 14:10
		((((laser with crystallization) and laser with anneal\$3) and	USPAT;	, 2003/01/03 14:10 , 2003/01/03 14:35
1	52	(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and	US-PGPUB;	2000/01/00 14.00
		clean\$4	EPO; JPO;	
1			DERWENT;	
1	i		IBM TDB	!

		<del>,</del>	
334	(((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)	USPAT; US-PGPUB;	2003/01/03 15:16
		EPO; JPO; DERWENT;	
		IBM_TDB	
- 249	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/01/03 14:43
	(silicon semiconductor)) and clean\$4)) and oxygen and	US-PGPUB;	
,	nitrogen	EPO; JPO; DERWENT;	f
		IBM_TDB	i.
- 264		USPAT;	2003/01/03 14:44
	(silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2")	US-PGPUB;	
	and (nitrogen "n.sub.2")	EPO; JPO; DERWENT;	i
		IBM_TDB	}
- 37	(((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 14:44
	(silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2")	US-PGPUB;	1
	and (nitrogen "n.sub.2")) and @ad<=19951025	EPO; JPO;	
		DERWENT; IBM_TDB	
52	((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:17
	(silicon semiconductor)) and clean\$4)) and (preheat\$3 (pre adj	US-PGPUB;	1
	heat\$3))	EPO; JPO;	1
		DERWENT;	1
- O	(((((laser with crystallization) and laser with anneal\$3) and	IBM_TDB USPAT;	2003/01/03 15:18
	(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	
	adj heat\$3)) with (oxygen "o.sub.2"))	EPO; JPO;	1
		DERWENT;	
15	(((((laser with crystallization) and laser with anneal\$3) and	IBM_TDB USPAT;	2003/01/03 15:20
40	(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	1 2000/0 //00 10:20
	adj heat\$3)) and (oxygen "o.sub.2"))	EPO; JPO;	:
		DERWENT;	
- 4	(((((((laser with crystallization) and laser with anneal\$3) and	IBM_TDB USPAT;	2003/01/03 15:18
7	(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	2000,01,00
	adj heat\$3)) and (oxygen "o.sub.2"))) and @ad<=19951025	EPO; JPO;	
		DERWENT;	
- 270	(((((laser with crystallization) and laser with anneal\$3) and	IBM_TDB USPAT;	2003/01/03 15:20
- 270	(((((laser with crystalization) and laser with afficeasts) and (silicon semiconductor)) and clean\$4)) and ((heat\$3) and	US-PGPUB;	2000/01/00 10:20
	(oxygen "o.sub.2"))	EPO; JPO;	
		DERWENT;	
- 62	(((((laser with crystallization) and laser with anneal\$3) and	IBM_TDB USPAT;	2003/01/03 15:20
- 02	(((((laser with crystalization) and clean\$4)) and ((heat\$3) with	US-PGPUB:	2003/01/03 13:20
	(oxygen "o.sub.2"))	EPO; JPO;	
		DERWENT;	
10	(////leaser with an intelligation) and leaser with appeal (2) and	IBM_TDB	2003/01/03 15:21
- 10	(((((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((heat\$3) with	USPAT; US-PGPUB;	2003/01/03 13.21
	(oxygen "o.sub.2"))) and @ad<=19951025	EPO; JPO;	1
	,,, C	DERWENT;	t •
1 400	la an an	IBM_TDB	2002/04/06 10:29
- 4493	laser with nitrogen	USPAT; US-PGPUB;	2003/01/06 10:28
		EPO; JPO;	1
		DERWENT;	t :
		IBM_TDB	0000/04/00 10 15
- 2978		USPAT;	2003/01/06 10:10
	or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.	US-PGPUB; EPO; JPO;	
	5. (1.116) 6. (11116) 6. (111116).00.00.	DERWENT;	
		IBM_TDB	

2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.269	USPAT; US-PGPUB; EPO; JPO;	
	(438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.	DERWENT;	• • • • • • • • • • • • • • • • • • •
73	(laser with nitrogen) and (((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or	USPAT; US-PGPUB; EPO; JPO;	2003/01/06 10:11
	(117/10)).CCLS.) ((laser with nitrogen) and (((438/166) or (438/905) or (438/487)	DERWENT; IBM_TDB USPAT;	2003/01/06 10:12
23	or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.)) and @ad<=19951025	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/00 10:12
1320	(((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/06 10:32
847	((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 11:46
258	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser) and anneal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/07 11:18
29	((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and oxidation with nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/06 10:47
14	(438/795) or (438/909) or (438/for 200) or (438/for 269) or (438/for 334) or (117/8) or (117/9) or (117/10)) CCLS.) and crystal\$ with silicon) and oxidation with nitrogen) and	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/06 11:45
48	@ad<=19951025 ((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser with air	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/06 11:47
18	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser with air) and @ad<=19951025	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/06 11:47
118	(laser with crystallization) and laser with air	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:18
16	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and (laser with air)) and anneal	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/07 11:19
4	((((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and (laser with air)) and anneal) and . @ad<=19951025	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:19